



LOW POWER NPN SILICON TRANSISTOR

Qualified per MIL-PRF-19500/391

Qualified Levels:
 JAN, JANTX,
 JANTXV, and JANS

DESCRIPTION

This 2N3057A NPN leaded silicon transistor device is military qualified for high-reliability applications. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N3057 number.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/391.
- Rad hard levels are also available per MIL-PRF-19500/391.
(For RHA datasheet see [JANS2N3057A](#).)
- RoHS compliant by design.

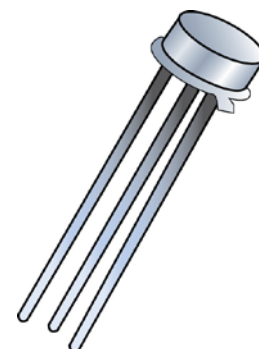
APPLICATIONS / BENEFITS

- Low profile metal TO-46 leaded package.
- Light weight.
- General-purpose switching and amplifier applications.
- Military and high-reliability applications.

MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise noted.

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-65 to +200	$^\circ\text{C}$
Thermal Impedance Junction-to-Ambient	$R_{\theta JA}$	325	$^\circ\text{C/W}$
Thermal Impedance Junction-to-Case	$R_{\theta JC}$	80	$^\circ\text{C/W}$
Collector-Emitter Voltage	V_{CEO}	80	V
Collector-Base Voltage	V_{CBO}	140	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current	I_C	1.0	A
Total Power Dissipation:	P_D	0.5	W
@ $T_A = +25^\circ\text{C}$ ⁽¹⁾ @ $T_C = +25^\circ\text{C}$ ⁽²⁾		1.8	

Notes: 1. Derate linearly 2.3 mW/ $^\circ\text{C}$ for $T_A \geq +25^\circ\text{C}$.
 2. Derate linearly 10.3 mW/ $^\circ\text{C}$ for $T_C \geq +25^\circ\text{C}$.



**TO-46 (TO-206AB)
Package**

Also available in:

TO-39 (TO-205AD)
 (short-leaded)
 [2N3019S](#)

TO-5 package
 (long-leaded)
 [2N3019](#)

TO-18 (TO-206AA)
 (leaded)
 [2N3700](#)

UB package
 (surface mount)
 [2N3700UB](#)

MSC – Lawrence

6 Lake Street,
 Lawrence, MA 01841
 Tel: 1-800-446-1158 or
 (978) 620-2600
 Fax: (978) 689-0803

MSC – Ireland

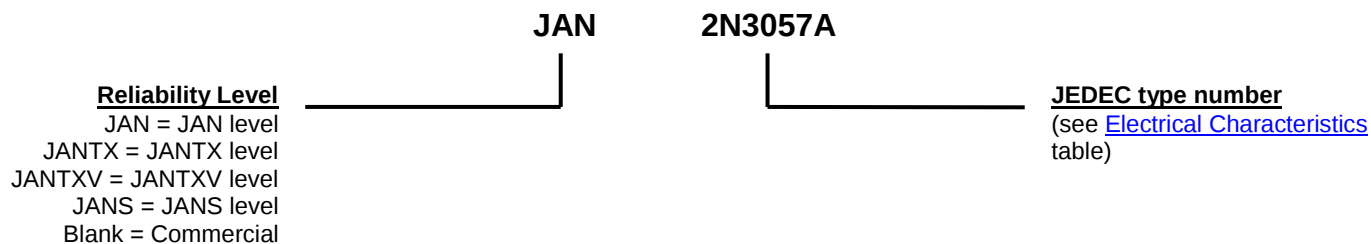
Gort Road Business Park,
 Ennis, Co. Clare, Ireland
 Tel: +353 (0) 65 6840044
 Fax: +353 (0) 65 6822298

Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Low profile nickel cap.
- TERMINALS: Gold over nickel plated kovar leads. Solder dip (Sn63/Pb37) available upon request. NOTE: Solder dip will eliminate RoHS compliance.
- MARKING: Part number, date code, manufacturer's ID and serial number.
- WEIGHT: Approximately 0.234 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE**SYMBOLS & DEFINITIONS**

Symbol	Definition
f	Frequency
I _B	Base current (dc)
I _E	Emitter current (dc)
T _A	Ambient temperature
T _C	Case temperature
V _{CB}	Collector to base voltage (dc)
V _{CE}	Collector to emitter voltage (dc)
V _{EB}	Emitter to base voltage (dc)

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted

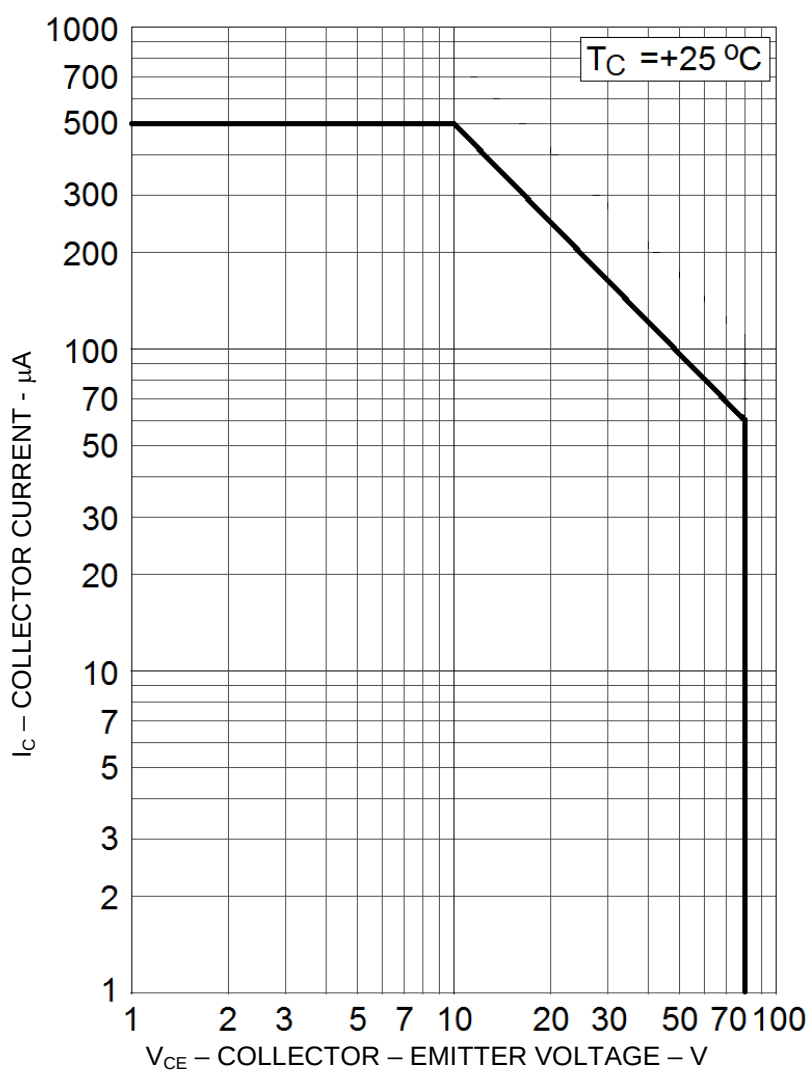
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Current $I_C = 30\text{ mA}$	$V_{(BR)CEO}$	80		V
Collector-Base Cutoff Current $V_{CB} = 140\text{ V}$	I_{CBO}		10	μA
Emitter-Base Cutoff Current $V_{EB} = 7\text{ V}$	I_{EBO1}		10	μA
Collector-Emitter Cutoff Current $V_{CE} = 90\text{ V}$	I_{CES}		10	ηA
Emitter-Base Cutoff Current $V_{EB} = 5.0\text{ V}$	I_{EBO2}		10	ηA
ON CHARACTERISTICS				
Forward-Current Transfer Ratio $I_C = 150\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 0.1\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}$, $V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ A}$, $V_{CE} = 10\text{ V}$	h_{FE}	100 50 90 50 15	300 300 300	
Collector-Emitter Saturation Voltage $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$		0.2 0.5	V
Base-Emitter Saturation Voltage $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$	$V_{BE(sat)}$		1.1	V

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$, $f = 1.0\text{ kHz}$	h_{fe}	80	400	
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 20\text{ MHz}$	$ h_{fe} $	5.0	20	
Output Capacitance $V_{CB} = 10\text{ V}$, $I_E = 0$, $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{obo}		12	pF
Input Capacitance $V_{EB} = 0.5\text{ V}$, $I_C = 0$, $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{ibo}		60	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted (continued)
SAFE OPERATION AREA (See SOA graph below and [MIL-STD-750, method 3053](#))

DC Tests
 $T_C = 25\text{ }^{\circ}\text{C}$, 1 cycle, $t = 10\text{ ms}$
Test 1
 $V_{CE} = 10\text{ V}$
 $I_C = 180\text{ mA}$
Test 2
 $V_{CE} = 40\text{ V}$
 $I_C = 45\text{ mA}$
Test 3
 $V_{CE} = 80\text{ V}$
 $I_C = 22.5\text{ mA}$

(1) Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

Maximum Safe Operating Area

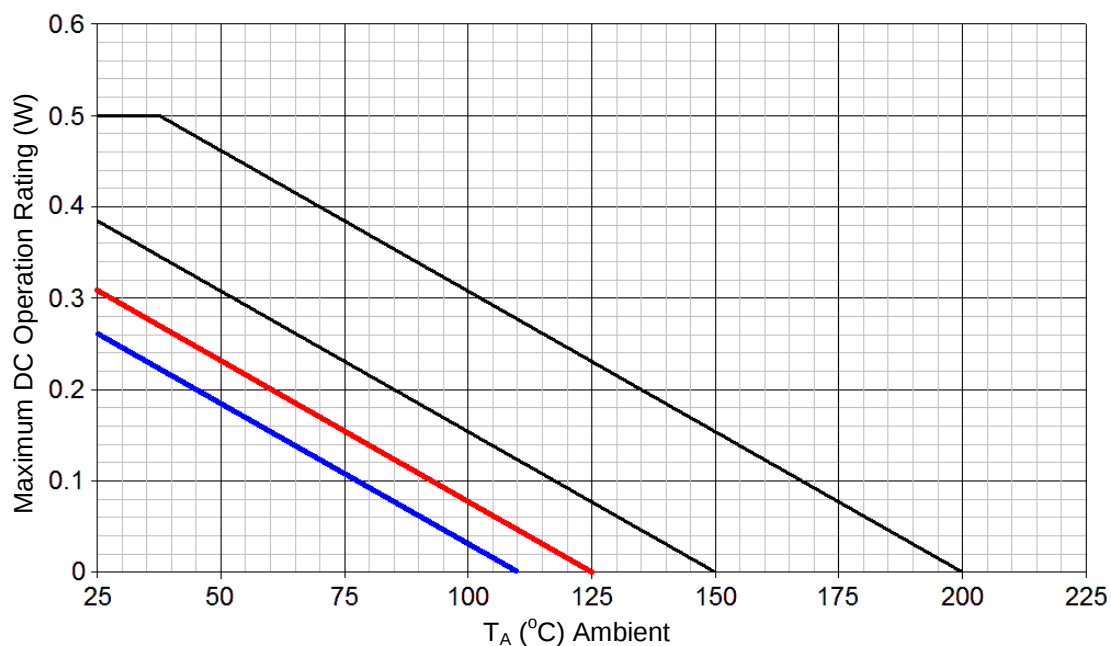
GRAPHS


FIGURE 1
Temperature-Power Derating (R_{θJA})
 Leads = .125 inch (3.175mm)

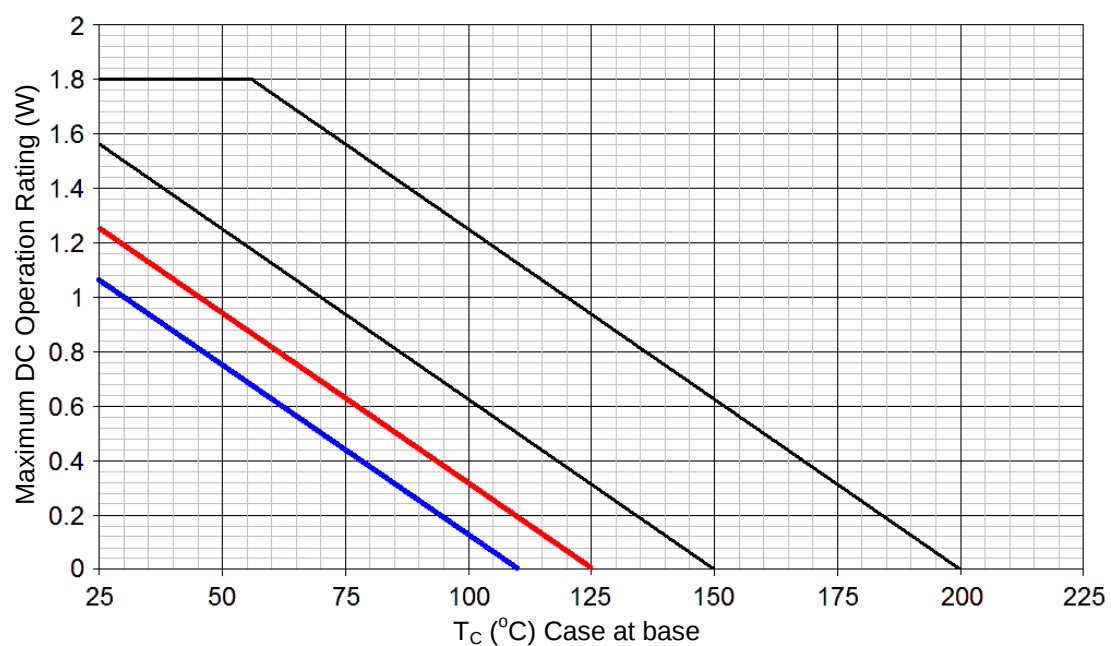
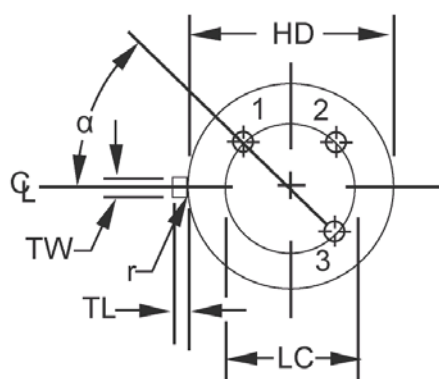
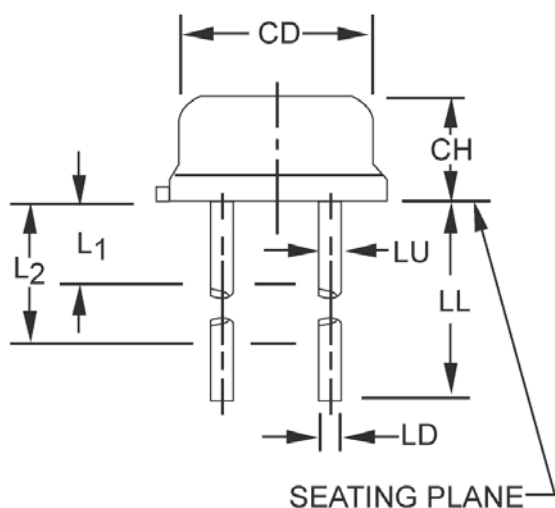


FIGURE 2
Temperature-Power Derating (R_{θJC})

PACKAGE DIMENSIONS


Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.065	.085	1.65	2.16	
HD	.209	.230	5.31	5.84	
LC	.100 TP		2.54 TP		6
LD	.016	.021	0.41	0.53	7
LL	.500	1.750	12.70	44.45	7
LU	.016	.019	0.41	0.48	7
L1		.050		1.27	7
L2	.250		6.35		7
TL	.028	.048	0.71	1.22	3
TW	.036	.046	0.91	1.17	2
r	-	.007	-	0.18	10, 11
α	45° TP		45° TP		6

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. This device may be measured by direct methods.
6. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
7. All three leads.
8. The collector shall be internally connected to the case.
9. Dimension r (radius) applies to both inside corners of tab.
10. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.
11. Lead 1 = emitter, lead 2 = base, lead 3 = collector.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9